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MR3029-81
Appl. No. 10/714,649
Reply to Office action of May 06, 2005



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Appl. No. : 10/714,649
Applicant : Shangir Gwo
Filed : November 18, 2003
TC/A.U. : 2818
Examiner : Dung A. LE
Title : METHOD FOR GROWING GROUP-III NITRIDE
SEMICONDUCTOR HETEROSTRUCTURE
ON SILICON SUBSTRATE

AMENDMENT AND RESPONSE

Commissioner for Patent
P. O. Box 1450
Alexandria VA 22313-1450

Sir:

In response to the Office Action of May 06, 2005, please amend the above-identified application as follows:

Amendments to the Specification begin on Page 2 of this paper

Amendments to the Claims are reflected in the listing of claims, which begins on Page 19 of this paper.

Remarks/Arguments begin on Page 24 of this paper.